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NPN SILICON RF TRANSISTOR NE46234 / 2SC4703

NPN EPITAXIAL SILICON RF TRANSISTOR FOR HIGH-FREQUENCY LOW DISTORTION AMPLIFIER 3-PIN POWER MINIMOLD

DESCRIPTION

The NE46234 / 2SC4703 is designed for low distortion, low noise RF amplifier operating with low supply voltage (Vce = 5 V). This low distortion characteristic makes it suitable for CATV, tele-communication and other use. It employs surface mount type plastic package, power mini mold (SOT-89).

FEATURES

- Low distortion, low voltage: IM₂ = 55 dBc TYP., IM₃ = 76 dBc TYP. @ VcE = 5 V, Ic = 50 mA, Vo = 105 dBμV/75Ω
- Large Ptot: Ptot = 1.8 W (Mounted on double-sided copper-clad 16 cm² × 0.7 mm (t) ceramic substrate)
- · Small package: 3-pin power mini mold package

ORDERING INFORMATION

Part Number	Quantity	Supplying Form
NE46234-AZ 2SC4703	25 pcs (Non reel)	• 12 mm wide embossed taping
NE46234-T1-AZ 2SC4703-T1	1 kpcs/reel	Collector face the perforation side of the tape

Remark To order evaluation samples, contact your nearby sales office. The unit sample quantity is 25 pcs.

ABSOLUTE MAXIMUM RATINGS (TA = +25°C)

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	Vcвo	25	٧
Collector to Emitter Voltage	VCEO	12	٧
Emitter to Base Voltage	V _{EBO}	2.5	٧
Collector Current	lc	150	mA
Total Power Dissipation	P _{tot} Note	1.8	W
Junction Temperature	Tj	150	°C
Storage Temperature	T _{stg}	−65 to +150	°C

Note Mounted on double-sided copper-clad 16 cm $^2 \times 0.7$ mm (t) ceramic substrate

Caution Observe precautions when handling because these devices are sensitive to electrostatic discharge.

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.

ELECTRICAL CHARACTERISTICS (TA = +25°C)

Parameter	Symbol	Test Conditions		MIN.	TYP.	MAX.	Unit
DC Characteristics							
Collector Cut-off Current	Ісво	V _{CB} = 20 V, I _E = 0 mA		_	_	1.5	μA
Emitter Cut-off Current	ІЕВО	V _{EB} = 2 V, I _C = 0 mA		-	-	1.5	μA
DC Current Gain	hfe Note 1	Vce = 5 V, Ic = 50 mA		50	-	250	_
RF Characteristics							
Gain Bandwidth Product	f⊤	Vce = 5 V, Ic = 50 mA		_	6.0	_	GHz
Insertion Power Gain (1)	S _{21e} ²	Vce = 5 V, Ic = 50 mA, f = 1 GHz		6.5	8.3	_	dB
Insertion Power Gain (2)	S _{21e} ²	Vce = 10 V, Ic = 20 mA, f = 1 GHz		-	8.5	-	dB
Noise Figure	NF	Vce = 5 V, Ic = 50 mA, f = 1 GHz		_	2.3	3.5	dB
Collector Capacitance	Cob Note 2	Vcb = 5 V, IE = 0 mA, f = 1 MHz		-	1.5	2.5	pF
2nd Order Intermoduration Distortion	IM ₂	Ic = 50 mA, Vo = 105 dB μ V/75 Ω, f = 190 – 90 MHz	Vce = 5 V	-	55	-	dBc
			Vce = 10 V		63	-	
3rd Order Intermoduration Distortion	IМз	Ic = 50 mA, Vo = 105 dB μ V/75 Ω , f = 2 × 190 – 200 MHz	Vce = 5 V	_	76	_	dBc
			Vce = 10 V	-	81	_	

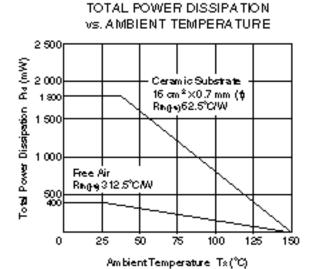
Notes 1. Pulse measurement: PW \leq 350 μ s, Duty Cycle \leq 2%

2. Collector to base capacitance when the emitter grounded

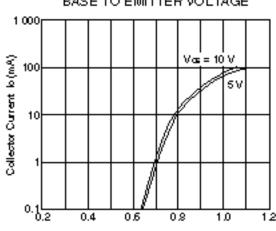
hfe CLASSIFICATION

Rank	SH	SF	SE
Marking	SH	SF	SE
hre Value	50 to 100	80 to 160	125 to 250

■ TYPICAL CHARACTERISTICS (TA = +25°C)

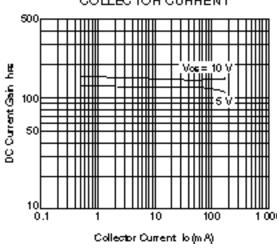




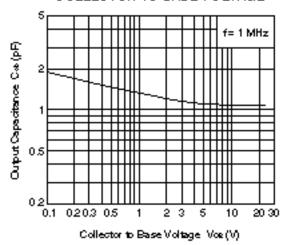


DC CURRENT GAIN vs.

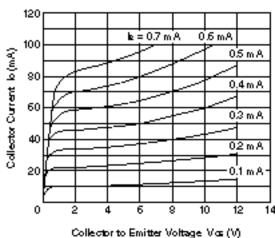
Base to Emitter Voltage Vas (V)



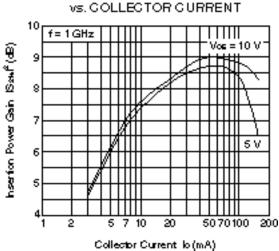
OUTPUT GAPACITANCE vs.
GOLLECTOR TO BASE VOLTAGE

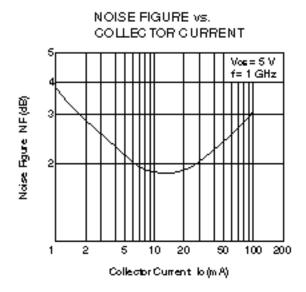


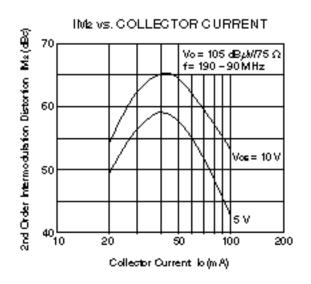
COLLECTOR CURRENT vs.
COLLECTOR TO EMITTER VOLTAGE

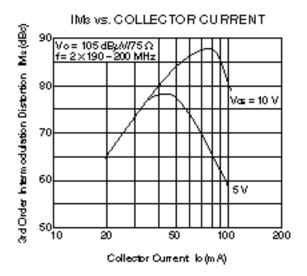


INSERTION POWER GAIN









Remark The graphs indicate nominal characteristics.

S-PARAMETERS

S-parameters/Noise parameters are provided on the NEC Compound Semiconductor Devices Web site in a form (SSP) that enables direct import to a microwave circuit simulator without keyboard input.

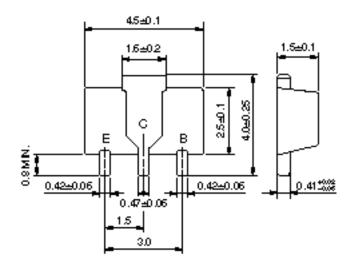
Click heire to download S-parameters.

[RF and Microwave] → [Device Parameters]

URL http://www.csd-nec.com/

PACKAGE DIMENSIONS

3-PIN POWER MINIMOLD (UNIT: mm)



PIN CONNECTIONS

E : Emitter C : Collector (Fin)

B : Base

(IEC: SOT-89)

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